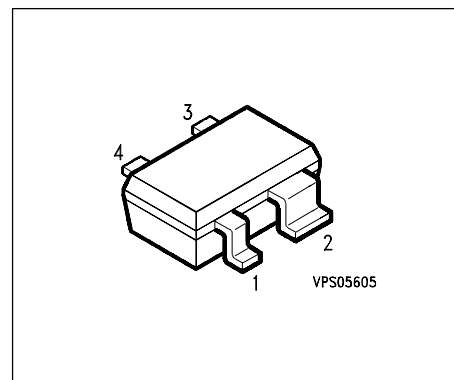


### NPN Silicon RF Transistor

- For low noise, high-gain broadband amplifiers at collector currents from 1mA to 20mA
- $f_T = 8\text{GHz}$   
 $F = 1.2\text{dB}$  at 900MHz



**ESD:** Electrostatic discharge sensitive device, observe handling precaution!

| Type     | Marking | Ordering Code | Pin Configuration |       |       |       | Package |
|----------|---------|---------------|-------------------|-------|-------|-------|---------|
| BFP 182W | RGs     | Q62702-F1502  | 1 = E             | 2 = C | 3 = E | 4 = B | SOT-343 |

### Maximum Ratings

| Parameter                                              | Symbol    | Values         | Unit |
|--------------------------------------------------------|-----------|----------------|------|
| Collector-emitter voltage                              | $V_{CEO}$ | 12             | V    |
| Collector-emitter voltage                              | $V_{CES}$ | 20             |      |
| Collector-base voltage                                 | $V_{CBO}$ | 20             |      |
| Emitter-base voltage                                   | $V_{EBO}$ | 2              |      |
| Collector current                                      | $I_C$     | 35             | mA   |
| Base current                                           | $I_B$     | 4              |      |
| Total power dissipation<br>$T_S \leq 91^\circ\text{C}$ | $P_{tot}$ | 250            | mW   |
| Junction temperature                                   | $T_j$     | 150            |      |
| Ambient temperature                                    | $T_A$     | - 65 ... + 150 |      |
| Storage temperature                                    | $T_{stg}$ | - 65 ... + 150 |      |

### Thermal Resistance

|                                          |            |            |     |
|------------------------------------------|------------|------------|-----|
| Junction - soldering point <sup>1)</sup> | $R_{thJS}$ | $\leq 235$ | K/W |
|------------------------------------------|------------|------------|-----|

1)  $T_S$  is measured on the collector lead at the soldering point to the pcb.

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

| Parameter                                                              | Symbol        | Values |      |      | Unit          |
|------------------------------------------------------------------------|---------------|--------|------|------|---------------|
|                                                                        |               | min.   | typ. | max. |               |
| DC Characteristics                                                     |               |        |      |      |               |
| Collector-emitter breakdown voltage<br>$I_C = 1\text{ mA}, I_B = 0$    | $V_{(BR)CEO}$ | 12     | -    | -    | V             |
| Collector-emitter cutoff current<br>$V_{CE} = 20\text{ V}, V_{BE} = 0$ | $I_{CES}$     | -      | -    | 100  | $\mu\text{A}$ |
| Collector-base cutoff current<br>$V_{CB} = 10\text{ V}, I_E = 0$       | $I_{CBO}$     | -      | -    | 100  | nA            |
| Emitter-base cutoff current<br>$V_{EB} = 1\text{ V}, I_C = 0$          | $I_{EBO}$     | -      | -    | 1    | $\mu\text{A}$ |
| DC current gain<br>$I_C = 10\text{ mA}, V_{CE} = 8\text{ V}$           | $h_{FE}$      | 50     | 100  | 200  | -             |

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

| Parameter                                                                                                                                        | Symbol         | Values |            |        | Unit |
|--------------------------------------------------------------------------------------------------------------------------------------------------|----------------|--------|------------|--------|------|
|                                                                                                                                                  |                | min.   | typ.       | max.   |      |
| AC Characteristics                                                                                                                               |                |        |            |        |      |
| Transition frequency<br>$I_C = 15\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $f = 500\text{ MHz}$                                                      | $f_T$          | 6      | 8          | -      | GHz  |
| Collector-base capacitance<br>$V_{CB} = 10\text{ V}$ , $f = 1\text{ MHz}$                                                                        | $C_{cb}$       | -      | 0.3        | 0.45   | pF   |
| Collector-emitter capacitance<br>$V_{CE} = 10\text{ V}$ , $f = 1\text{ MHz}$                                                                     | $C_{ce}$       | -      | 0.27       | -      |      |
| Emitter-base capacitance<br>$V_{EB} = 0.5\text{ V}$ , $f = 1\text{ MHz}$                                                                         | $C_{eb}$       | -      | 0.6        | -      |      |
| Noise figure<br>$I_C = 3\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_{Sopt}$<br>$f = 900\text{ MHz}$<br>$f = 1.8\text{ GHz}$                   | $F$            | -<br>- | 1.2<br>1.9 | -<br>- | dB   |
| Power gain 1)<br>$I_C = 10\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $f = 900\text{ MHz}$<br>$Z_S = Z_{Sopt}$ , $Z_L = Z_{Lopt}$                      | $G_{ms}$       | -      | 21.5       | -      |      |
| Power gain 2)<br>$I_C = 10\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $f = 1.8\text{ GHz}$<br>$Z_S = Z_{Sopt}$ , $Z_L = Z_{Lopt}$                      | $G_{ma}$       | -      | 15.5       | -      |      |
| Transducer gain<br>$I_C = 10\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_L = 50\text{ }\Omega$<br>$f = 900\text{ MHz}$<br>$f = 1.8\text{ GHz}$ | $ S_{21el} ^2$ | -<br>- | 17.5<br>12 | -<br>- |      |

1)  $G_{ms} = |S_{21}/S_{12}|$

2)  $G_{ma} = |S_{21}/S_{12}| (k - (k^2 - 1)^{1/2})$

**SPICE Parameters (Gummel-Poon Model, Berkeley-SPICE 2G.6 Syntax) :****Transistor Chip Data**

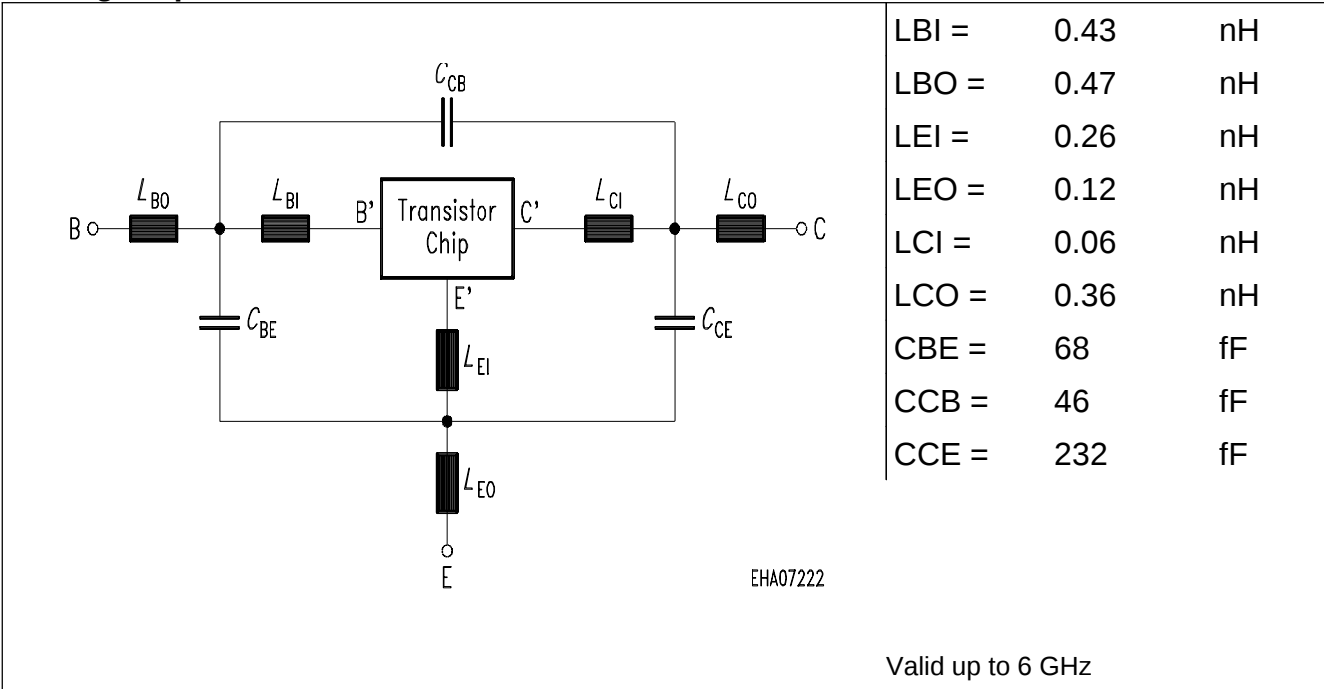
|       |         |          |       |          |          |        |          |          |
|-------|---------|----------|-------|----------|----------|--------|----------|----------|
| IS =  | 4.8499  | fA       | BF =  | 84.113   | -        | NF =   | 0.56639  | -        |
| VAF = | 21.742  | V        | IKF = | 0.14414  | A        | ISE =  | 8.4254   | fA       |
| NE =  | 0.91624 | -        | BR =  | 10.004   | -        | NR =   | 0.54818  | -        |
| VAR = | 2.2595  | V        | IKR = | 0.039478 | A        | ISC =  | 5.9438   | fA       |
| NC =  | 0.5641  | -        | RB =  | 2.8263   | $\Omega$ | IRB =  | 0.071955 | mA       |
| RBM = | 3.4217  | $\Omega$ | RE =  | 2.1858   | $\Omega$ | RC =   | 1.8159   | $\Omega$ |
| CJE = | 8.8619  | fF       | VJE = | 1.0378   | V        | MJE =  | 0.40796  | -        |
| TF =  | 22.72   | ps       | XTF = | 0.43147  | -        | VTF =  | 0.34608  | V        |
| ITF = | 6.5523  | mA       | PTF = | 0        | deg      | CJC =  | 490.25   | fF       |
| VJC = | 1.0132  | V        | MJC = | 0.31068  | -        | XCJC = | 0.19281  | -        |
| TR =  | 1.7541  | ns       | CJS = | 0        | fF       | VJS =  | 0.75     | V        |
| MJS = | 0       | -        | XTB = | 0        | -        | EG =   | 1.11     | eV       |
| XTI = | 3       | -        | FC =  | 0.64175  | -        | TNOM   | 300      | K        |

All parameters are ready to use, no scaling is necessary.

Extracted on behalf of SIEMENS Small Signal Semiconductors by:

Institut für Mobil-und Satellitenfunktechnik (IMST)

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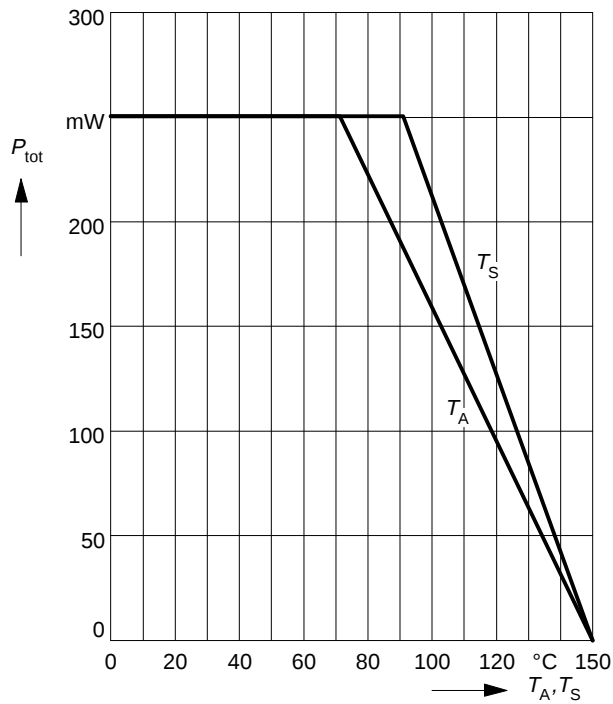
**Package Equivalent Circuit:**

|       |      |    |
|-------|------|----|
| LBI = | 0.43 | nH |
| LBO = | 0.47 | nH |
| LEI = | 0.26 | nH |
| LEO = | 0.12 | nH |
| LCI = | 0.06 | nH |
| LCO = | 0.36 | nH |
| CBE = | 68   | fF |
| CCB = | 46   | fF |
| CCE = | 232  | fF |

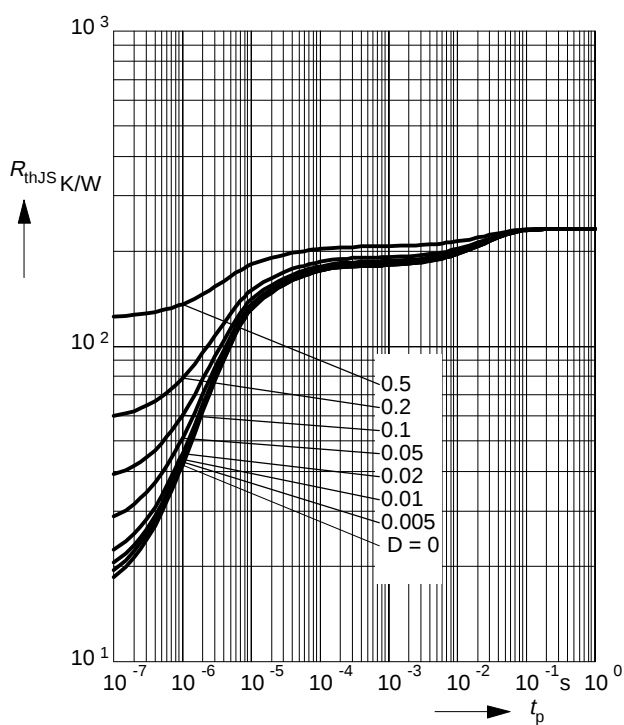
For examples and ready to use parameters please contact your local Siemens distributor or sales office to obtain a Siemens CD-ROM or see Internet: <http://www.siemens.de/Semiconductor/products/35/35.htm>

**Total power dissipation**  $P_{\text{tot}} = f(T_A^*, T_S)$

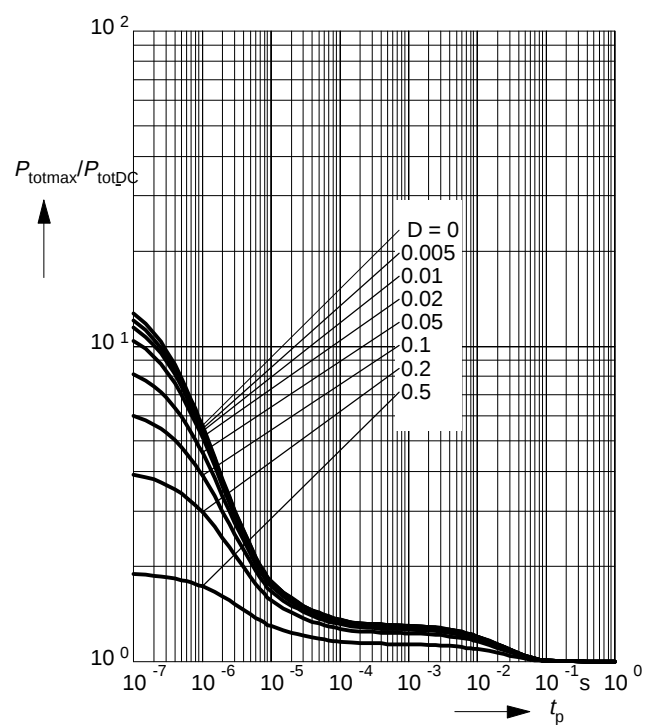
\* Package mounted on epoxy



**Permissible Pulse Load**  $R_{\text{thJS}} = f(t_p)$

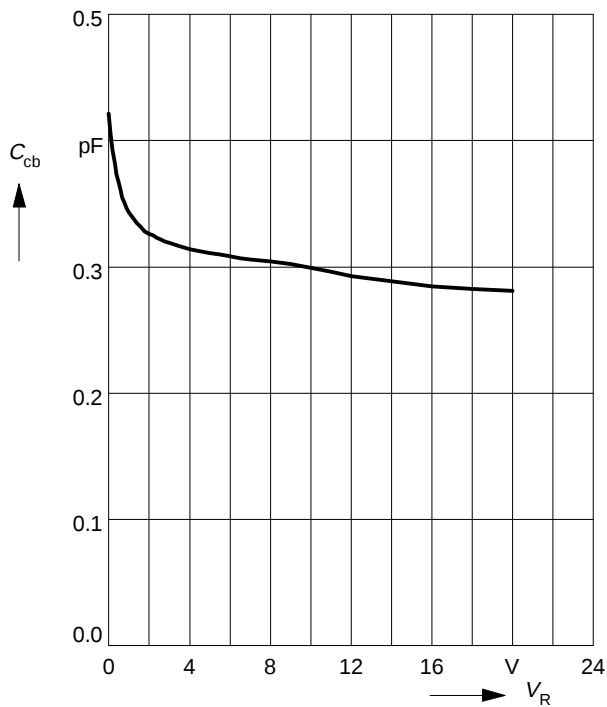


**Permissible Pulse Load**  $P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$



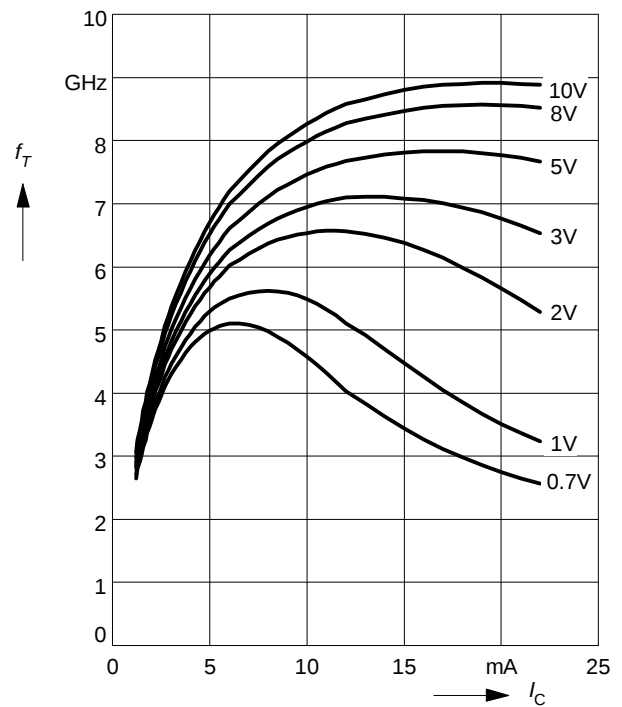
## Collector-base capacitance $C_{cb} = f(V_{CB})$

$V_{BE} = v_{be} = 0, f = 1\text{MHz}$



## Transition frequency $f_T = f(I_C)$

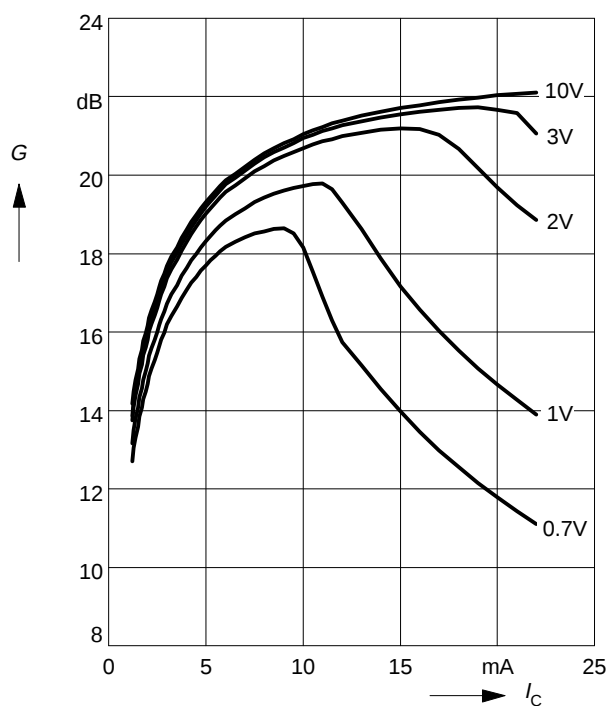
$V_{CE} = \text{Parameter}$



## Power Gain $G_{ma}, G_{ms} = f(I_C)$

$f = 0.9\text{GHz}$

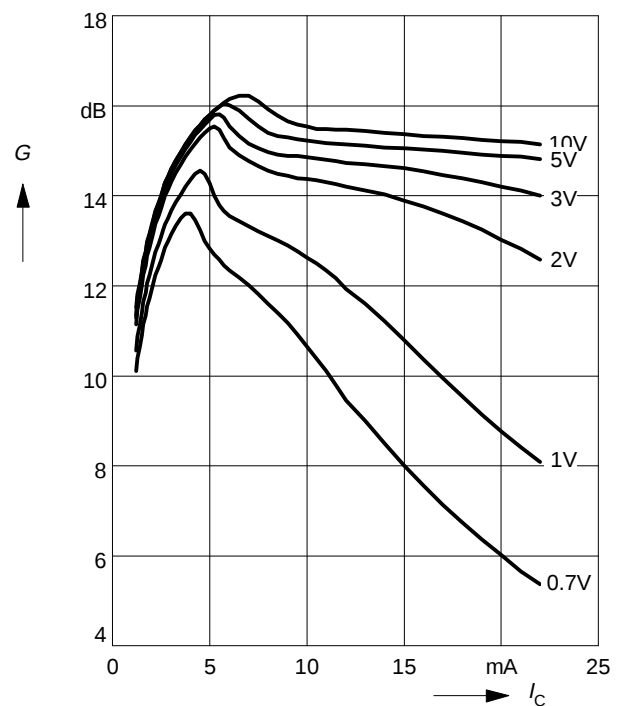
$V_{CE} = \text{Parameter}$



## Power Gain $G_{ma}, G_{ms} = f(I_C)$

$f = 1.8\text{GHz}$

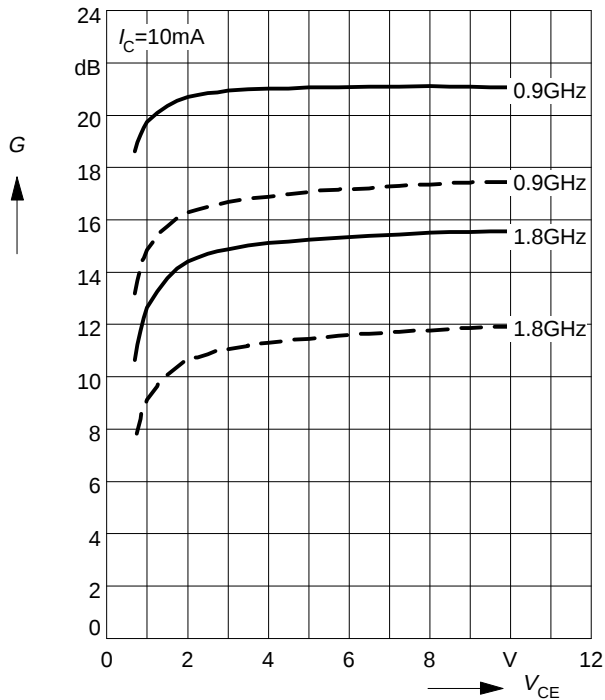
$V_{CE} = \text{Parameter}$



**Power Gain**  $G_{ma}$ ,  $G_{ms} = f(V_{CE})$ : \_\_\_\_\_

$|S_{21}|^2 = f(V_{CE})$ : -----

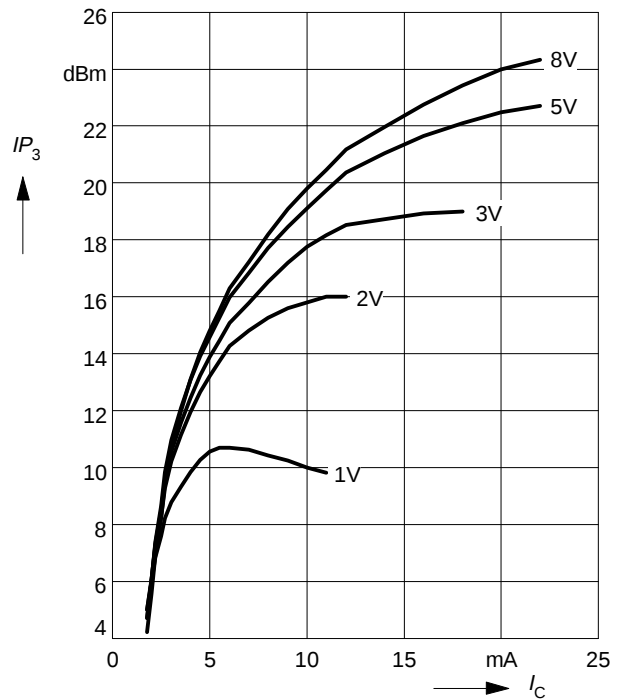
$f$  = Parameter



**Intermodulation Intercept Point**  $IP_3 = f(I_C)$

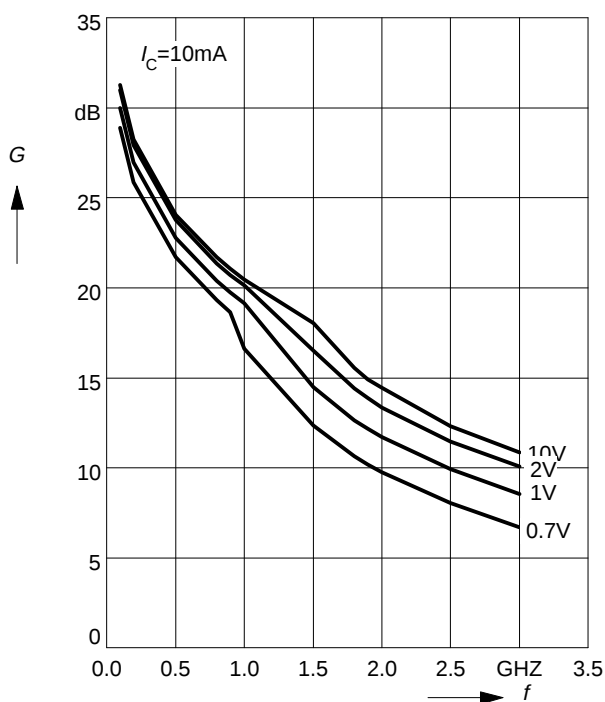
(3rd order, Output,  $Z_S = Z_L = 50\Omega$ )

$V_{CE}$  = Parameter,  $f = 900\text{MHz}$



**Power Gain**  $G_{ma}$ ,  $G_{ms} = f(f)$

$V_{CE}$  = Parameter



**Power Gain**  $|S_{21}|^2 = f(f)$

$V_{CE}$  = Parameter

